

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Currently Amended) A method of forming a fine pattern, comprising[[,]] :
  - a lithography step for forming a resist pattern on a film to be processed deposited on a substrate using a lithography technique,
  - a first etching step for etching said resist pattern to narrow the line width of said resist pattern,
  - a second etching step for performing anisotropic etching to a first film to be processed underneath said resist pattern, under a reduced pressure environment where the etching rate of an exposed area of the first film in the vicinity of the side of said resist pattern is higher than the etching rate of other exposed areas of the first film, to expose a second film to be processed underneath said first film to be processed in the vicinity of the side of the line of said resist pattern, and to form the pattern of said first film to be processed, and
  - a third etching step for etching said second film to be processed using the pattern of said first film to be processed as a mask, to form a pattern of a pitch of 1/2 the pitch of said resist pattern on said second film to be processed.
2. (Currently Amended) The method of forming a fine pattern according to claim 1, wherein said reduced pressure environment is an environment where the pressure of the etching gas is 1.5 Pa or below.
3. (Original) The method of forming a fine pattern according to claim 1, wherein said first film to be processed is a nitride film, and said second film to be processed is an oxide film.
4. (Original) The method of forming a fine pattern according to claim 1, wherein said third etching step is a step for performing anisotropic etching to said second film to be

processed using the pattern of said first film to be processed as a mask, then performing isotropic etching to obtain a pattern of a desired line width and space width.

5. (Original) The method of forming a fine pattern according to claim 1, further comprising a fourth etching step, wherein anisotropic etching is performed to said third film to be processed underneath said second film to be processed using the pattern obtained by said third etching step as a mask, to form a desired line width and space width on said third film to be processed.

6. (Original) A method of manufacturing a semiconductor device comprising steps for forming a fine pattern using the method of forming a fine pattern according to claim 1.

7. (Original) A semiconductor device manufactured using the method of manufacturing a semiconductor device according to claim 6.